

QM4015S

P-Channel 40V Fast Switching MOSFET

General Description

The QM4015S is a high performance trench P-channel MOSFET which utilizes extremely high cell density to provide low R_{DS(on)} and gate charge characteristics. It is ideally suited to support synchronous buck converter applications.

The QM4015S meets RoHS and Green Product requirements while supporting full function reliability.

Features

- ✓ Advanced high cell density Trench technology
- ✓ Super Low Gate Charge
- ✓ Excellent CdV/dt effect decline
- ✓ Green Device Available

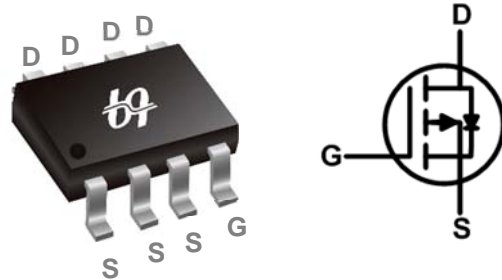
Product Summary

V _{DS}	R _{DS(ON)} max (V _{GS} =-10V)	I _D (T _A =25 °C)
-40V	13mΩ	-8.7A

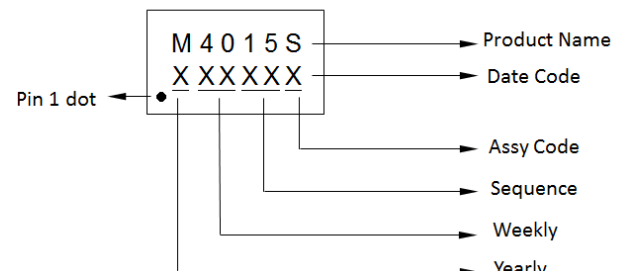
Applications

- ✓ High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- ✓ Networking DC-DC Power System
- ✓ Load Switch

Pin Configuration



Ordering Information

Order Number	Package Type	Top Marking
QM4015S	SOP8	

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Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-8.7	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-7	A
I_{DM}	Pulsed Drain Current ²	-18	A
EAS	Single Pulse Avalanche Energy ³	262	mJ
I_{AS}	Avalanche Current	-54	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	--	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	--	24	$^\circ C/W$

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P-Channel Electrical Characteristics

P-Channel Electrical Characteristics: (T _J =25 °C, unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	--	--	V
ΔBV _{DSS} / ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =-1mA	--	-0.023	--	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-8A	--	10.5	13	mΩ
		V _{GS} =-4.5V, I _D =-6A	--	16	20	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.6	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		--	4.74	--	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-32V, V _{GS} =0V, T _J =25°C	--	--	-1	uA
		V _{DS} =-32V, V _{GS} =0V, T _J =55°C	--	--	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-8A	--	27	--	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	--	7	14	Ω
Q _g	Total Gate Charge	V _{DS} =-20V, V _{GS} =-4.5V, I _D =-6A	--	28	--	nC
Q _{gs}	Gate-Source Charge		--	7.7	--	
Q _{gd}	Gate-Drain Charge		--	7.5	--	
t _{d(on)}	Turn-On Delay Time	V _{DS} =-15V, V _{GS} =-10V, R _G =3.3Ω, I _D =-6A	--	10	--	ns
t _r	Rise Time		--	35	--	
t _{d(off)}	Turn-Off Delay Time		--	110	--	
t _f	Fall Time		--	47	--	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	3500	--	pF
C _{oss}	Output Capacitance		--	323	--	
C _{rss}	Reverse Transfer Capacitance		--	222	--	

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Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	$V_{DD}=-25V$, $L=0.1mH$, $I_{AS}=-30A$	81	--	--	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	--	--	-8.7	A
I_{SM}	Pulsed Source Current ^{2,6}		--	--	-18	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ C$	--	--	-1	V

Note:

1. Test data conducted with surface mount attachment to 1 inch², FR-4 board utilizing 2oz copper
2. Pulse Test. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. EAS data is a maximum rating. The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH$
4. The power dissipation is limited by a 150°C maximum junction temperature
5. The Min. value is 100% EAS tested guarantee
6. The data is theoretically the same as I_D and I_{DM} . In real applications, it will be limited by total power

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Typical Characteristics

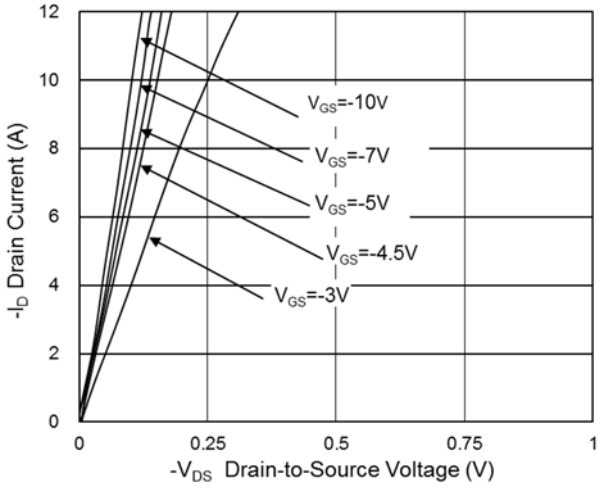


Fig.1: Typical Output Characteristics

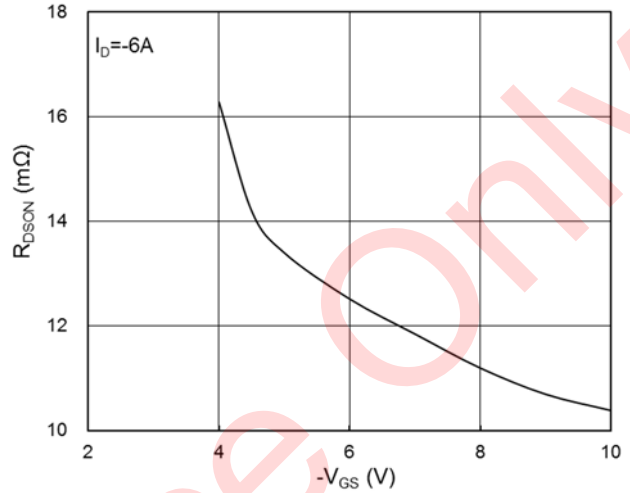


Fig.2: On-Resistance vs. Gate-Source

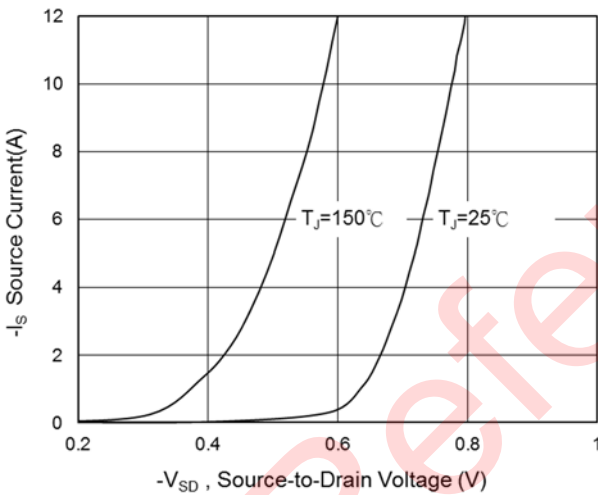


Fig.3: Forward Characteristics of Reverse

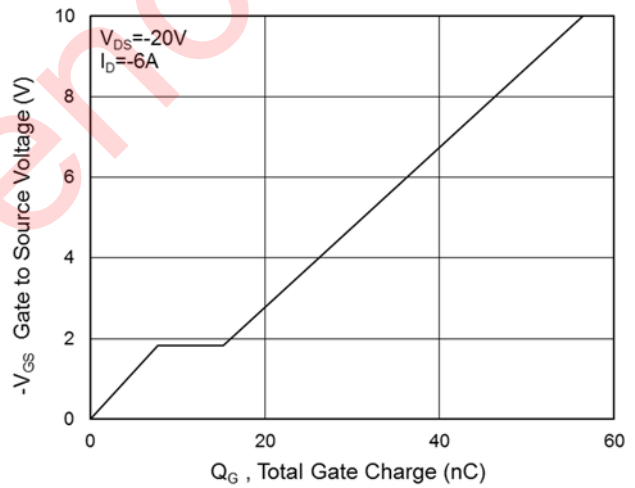


Fig.4: Gate-Charge Characteristics

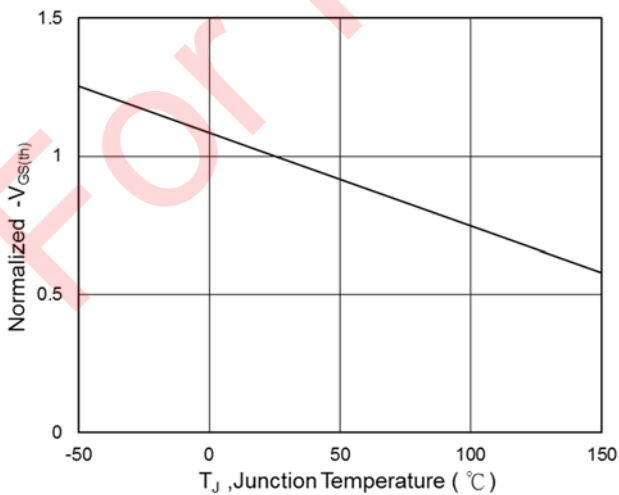


Fig.5: Normalized $V_{GS(th)}$ vs. T_J

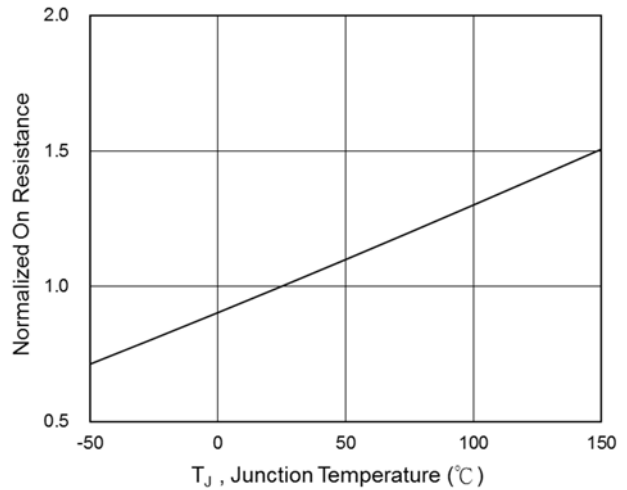


Fig.6: Normalized $R_{DS(on)}$ vs. T_J

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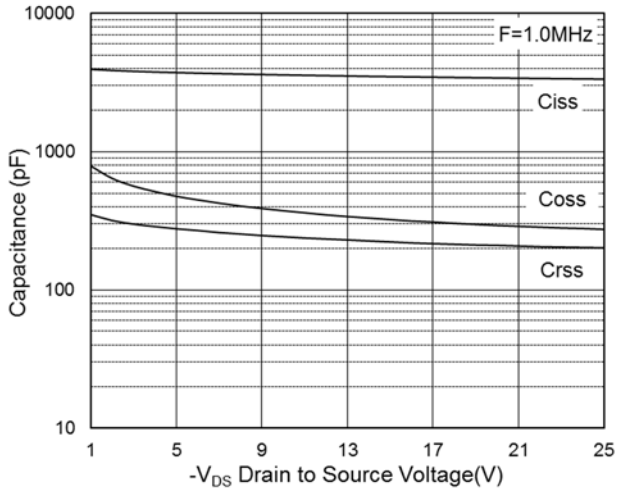


Fig.7: Capacitance

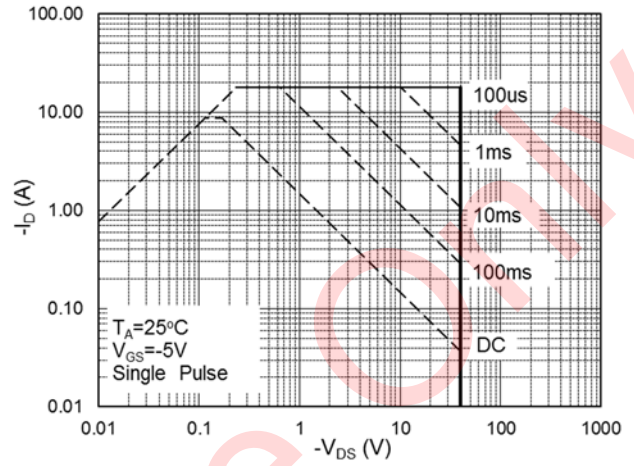


Fig.8: Safe Operating Area

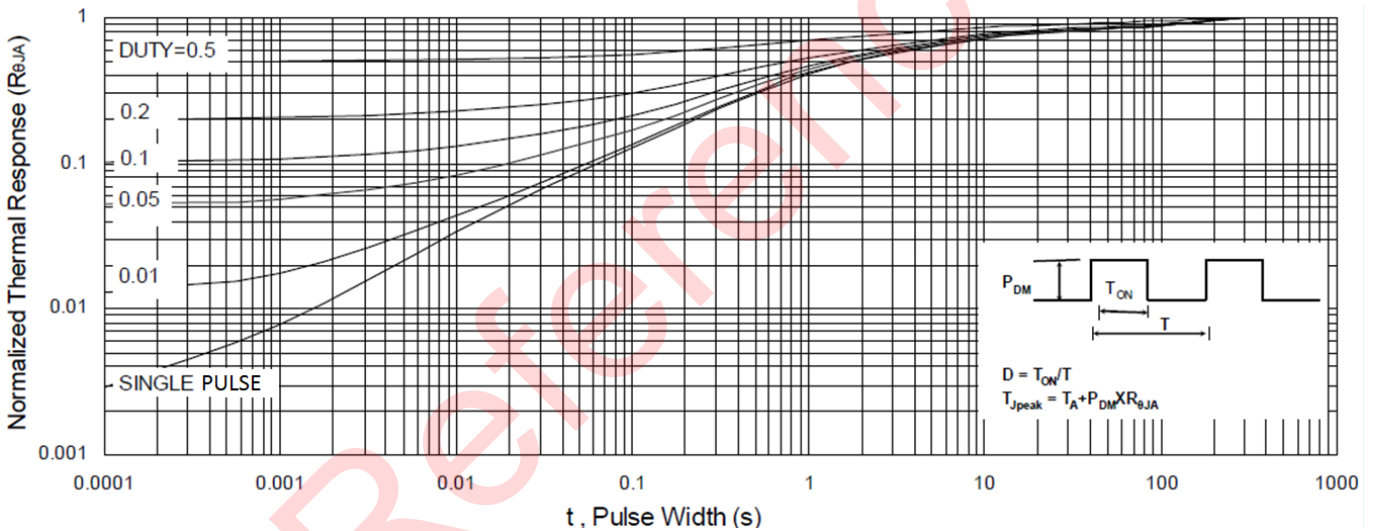


Fig.9: Normalized Maximum Transient Thermal Impedance

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uPI Semiconductor Corp.

9F.,No.5, Taiyuan 1st St. Zhubei City, Hsinchu, Taiwan, R.O.C.

TEL : 886.3.560.1666 FAX : 886.3.560.1888

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